Dual bus buffer/line driver; 3-state Rev. 14 — 29 March 2013

Product data sheet

General description 1.

The 74LVC2G125 provides a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (pin nOE). A HIGH-level at pin nOE causes the output to assume a high-impedance OFF-state. Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low-power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

| Type number | Package | | | |
|--------------|-------------------|--------|---|----------|
| | Temperature range | Name | Description | Version |
| 74LVC2G125DP | –40 °C to +125 °C | TSSOP8 | plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm | SOT505-2 |
| 74LVC2G125DC | –40 °C to +125 °C | VSSOP8 | plastic very thin shrink small outline package; 8 leads; body width 2.3 mm | SOT765-1 |
| 74LVC2G125GT | –40 °C to +125 °C | XSON8 | plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm | SOT833-1 |
| 74LVC2G125GF | –40 °C to +125 °C | XSON8 | extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm | SOT1089 |
| 74LVC2G125GD | –40 °C to +125 °C | XSON8 | plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm | SOT996-2 |
| 74LVC2G125GM | –40 °C to +125 °C | XQFN8 | plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm | SOT902-2 |
| 74LVC2G125GN | –40 °C to +125 °C | XSON8 | extremely thin small outline package; no leads; 8 terminals; body 1.2 \times 1.0 \times 0.35 mm | SOT1116 |
| 74LVC2G125GS | –40 °C to +125 °C | XSON8 | extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm | SOT1203 |

4. Marking

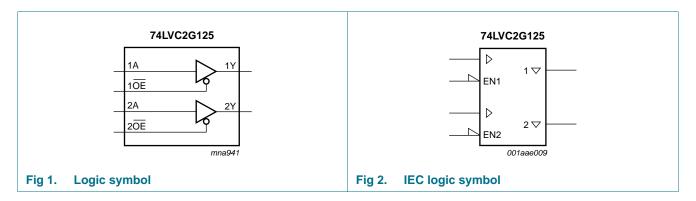
Table 2. Marking codes

| Type number | Marking code ^[1] |
|--------------|-----------------------------|
| 74LVC2G125DP | V25 |
| 74LVC2G125DC | V25 |
| 74LVC2G125GT | V25 |
| 74LVC2G125GF | VM |
| 74LVC2G125GD | V25 |
| 74LVC2G125GM | V25 |
| 74LVC2G125GN | VM |
| 74LVC2G125GS | VM |

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

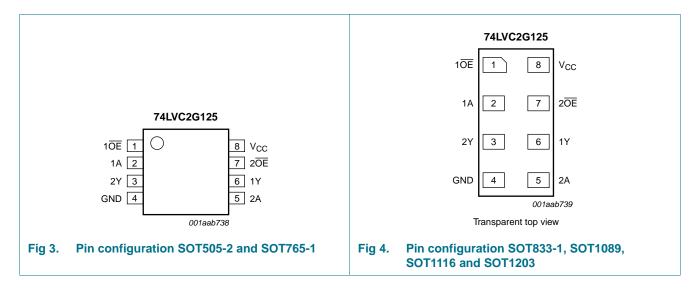
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5. Functional diagram

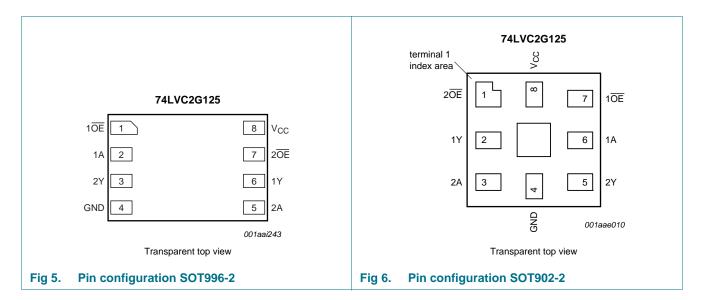


6. Pinning information

6.1 Pinning



Dual bus buffer/line driver; 3-state



6.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description | | |
|-----------------|--|-------------|----------------------------------|--|
| | SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203 | SOT902-2 | | |
| 10E, 20E | 1, 7 | 7, 1 | output enable input (active LOW) | |
| 1A, 2A | 2, 5 | 6, 3 | data input | |
| GND | 4 | 4 | ground (0 V) | |
| 1Y, 2Y | 6, 3 | 2, 5 | data output | |
| V _{CC} | 8 | 8 | supply voltage | |

7. Functional description

Table 4. Function table[1]

| Control nOE | Input | Output |
|----------------|-------|--------|
| nOE | nA | nY |
| L | L | L |
| L | Н | Н |
| Н | X | Z |

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|--|-----------------|----------------|------|
| V_{CC} | supply voltage | | -0.5 | +6.5 | V |
| I _{IK} | input clamping current | V _I < 0 V | -50 | - | mA |
| VI | input voltage | | <u>[1]</u> –0.5 | +6.5 | V |
| I _{OK} | output clamping current | $V_O > V_{CC}$ or $V_O < 0 V$ | - | ±50 | mA |
| Vo | output voltage | Enable mode | <u>[1]</u> –0.5 | $V_{CC} + 0.5$ | V |
| | | Disable mode | <u>[1]</u> –0.5 | +6.5 | V |
| | | Power-down mode | [1][2] -0.5 | +6.5 | V |
| Io | output current | $V_O = 0 V \text{ to } V_{CC}$ | - | ±50 | mA |
| I _{CC} | supply current | | - | 100 | mA |
| I_{GND} | ground current | | -100 | - | mA |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| P _{tot} | total power dissipation | $T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$ | <u>[3]</u> _ | 300 | mW |

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|---|------|----------|------|
| V_{CC} | supply voltage | | 1.65 | 5.5 | V |
| V_{I} | input voltage | | 0 | 5.5 | V |
| Vo | output voltage | V _{CC} = 1.65 V to 5.5 V; Enable mode | 0 | V_{CC} | V |
| | | V _{CC} = 1.65 V to 5.5 V; Disable mode | 0 | 5.5 | V |
| | | V _{CC} = 0 V; Power-down mode | 0 | 5.5 | V |
| T _{amb} | ambient temperature | | -40 | +125 | °C |
| Δt/ΔV | input transition rise and | V _{CC} = 1.65 V to 2.7 V | - | 20 | ns/V |
| | fall rate | V _{CC} = 2.7 V to 5.5 V | - | 10 | ns/V |
| | | | | | |

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8, XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

| Symbol | Parameter | Conditions | Min | Typ[1] | Max | Unit |
|----------------------|---------------------------|---|-----------------------|--------|--------------|------|
| T _{amb} = - | 40 °C to +85 °C | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 1.65 V to 1.95 V | 0.65V _{CC} | - | - | V |
| | | V _{CC} = 2.3 V to 2.7 V | 1.7 | - | - | V |
| | | V _{CC} = 2.7 V to 3.6 V | 2.0 | - | - | V |
| | | V _{CC} = 4.5 V to 5.5 V | $0.7V_{CC}$ | - | - | V |
| V_{IL} | LOW-level input voltage | V _{CC} = 1.65 V to 1.95 V | - | - | $0.35V_{CC}$ | V |
| | | V _{CC} = 2.3 V to 2.7 V | - | - | 0.7 | V |
| | | V _{CC} = 2.7 V to 3.6 V | - | - | 8.0 | V |
| | | V _{CC} = 4.5 V to 5.5 V | - | - | $0.3V_{CC}$ | V |
| V _{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V | - | - | 0.1 | V |
| | | $I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$ | - | - | 0.45 | V |
| | | $I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.3 | V |
| | | $I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$ | - | - | 0.4 | V |
| | | $I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.55 | V |
| | | $I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | - | - | 0.55 | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $I_O = -100 \mu A$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$ | V _{CC} - 0.1 | - | - | V |
| | | $I_{O} = -4 \text{ mA}$; $V_{CC} = 1.65 \text{ V}$ | 1.2 | - | - | V |
| | | $I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.9 | - | - | V |
| | | $I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$ | 2.2 | - | - | V |
| | | $I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.3 | - | - | V |
| | | $I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | 3.8 | - | - | V |
| I _I | input leakage current | $V_I = 5.5 \text{ V or GND}$; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ | - | ±0.1 | ±5 | μΑ |
| I _{OZ} | OFF-state output current | $V_I = V_{IH}$ or V_{IL} ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V | - | ±0.1 | ±10 | μΑ |
| I _{OFF} | power-off leakage current | V_I or $V_O = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$ | - | ±0.1 | ±10 | μΑ |
| I _{CC} | supply current | $V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$ | - | 0.1 | 10 | μΑ |
| ΔI_{CC} | additional supply current | per pin; $V_I = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V | - | 5 | 500 | μΑ |
| C _I | input capacitance | | - | 2 | - | pF |

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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

| Symbol | Parameter | Conditions | Min | Typ[1] | Max | Unit |
|----------------------|---------------------------|---|-----------------------|--------|--------------|------|
| T _{amb} = - | 40 °C to +125 °C | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 1.65 V to 1.95 V | 0.65V _{CC} | - | - | V |
| | | V _{CC} = 2.3 V to 2.7 V | 1.7 | - | - | V |
| | | V _{CC} = 2.7 V to 3.6 V | 2.0 | - | - | V |
| | | V _{CC} = 4.5 V to 5.5 V | 0.7V _{CC} | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 1.65 V to 1.95 V | - | - | $0.35V_{CC}$ | V |
| | | V _{CC} = 2.3 V to 2.7 V | - | - | 0.7 | V |
| | | V _{CC} = 2.7 V to 3.6 V | - | - | 8.0 | V |
| | | V _{CC} = 4.5 V to 5.5 V | - | - | $0.3V_{CC}$ | V |
| V _{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V | - | - | 0.1 | V |
| | | $I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$ | - | - | 0.70 | V |
| | | $I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.45 | V |
| | | $I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$ | - | - | 0.60 | V |
| | | $I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.80 | V |
| | | $I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | - | - | 0.80 | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $I_{O} = -100 \ \mu A; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$ | V _{CC} - 0.1 | - | - | V |
| | | $I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$ | 0.95 | - | - | V |
| | | $I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.7 | - | - | V |
| | | $I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$ | 1.9 | - | - | V |
| | | $I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.0 | - | - | V |
| | | $I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | 3.4 | - | - | V |
| l _l | input leakage current | $V_I = 5.5 \text{ V or GND}$; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ | - | - | ±20 | μΑ |
| l _{oz} | OFF-state output current | $V_I = V_{IH}$ or V_{IL} ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V | - | - | ±20 | μΑ |
| OFF | power-off leakage current | V_{I} or $V_{O} = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$ | - | - | ±20 | μΑ |
| CC | supply current | $V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to 5.5 V}; I_O = 0 \text{ A}$ | - | - | 40 | μΑ |
| ∆l _{CC} | additional supply current | per pin; $V_1 = V_{CC} - 0.6 \text{ V}$; $I_O = 0 \text{ A}$; $V_{CC} = 2.3 \text{ V}$ to 5.5 V | - | - | 5 | mA |

^[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

| Symbol | Parameter | Conditions | | -40 | °C to +85 | °C | -40 °C t | Unit | |
|-----------------------------------|--|--|------------|-----|-----------|------|----------|------|----|
| | | | | Min | Typ[1] | Max | Min | Max | |
| t _{pd} propagation delay | | nA to nY; see Figure 7 | [2] | | | | | | |
| | | $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ | | 1.0 | 3.7 | 9.1 | 1.0 | 11.4 | ns |
| | | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | | 0.5 | 2.5 | 4.8 | 0.5 | 6.0 | ns |
| | | $V_{CC} = 2.7 \text{ V}$ | | 1.0 | 2.7 | 4.8 | 1.0 | 6.0 | ns |
| | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | | 0.5 | 2.3 | 4.3 | 0.5 | 5.5 | ns | |
| | | $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ | | 0.5 | 1.9 | 3.7 | 0.5 | 4.6 | ns |
| t _{en} enable time | | nOE to nY; see Figure 8 | [3] | | | | | | |
| | | $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ | | 1.5 | 4.3 | 9.9 | 1.5 | 12.4 | ns |
| | | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | | 1.0 | 2.8 | 5.6 | 1.0 | 7.0 | ns |
| | | $V_{CC} = 2.7 \text{ V}$ | | 1.5 | 3.3 | 5.7 | 1.5 | 7.1 | ns |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | | 0.5 | 2.4 | 4.7 | 0.5 | 5.9 | ns |
| | | $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ | | 0.5 | 2.0 | 3.8 | 0.5 | 4.8 | ns |
| t _{dis} | disable time | nOE to nY; see Figure 8 | <u>[4]</u> | | | | | | |
| | | $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ | | 1.0 | 3.5 | 11.6 | 1.0 | 14.1 | ns |
| | | $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ | | 0.5 | 1.8 | 5.8 | 0.5 | 7.6 | ns |
| | | $V_{CC} = 2.7 \text{ V}$ | | 1.0 | 2.7 | 4.8 | 1.0 | 6.2 | ns |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | | 1.0 | 2.7 | 4.6 | 1.0 | 5.9 | ns |
| | | $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ | | 0.5 | 1.8 | 3.4 | 0.5 | 4.6 | ns |
| C_{PD} | power dissipation | per buffer; $V_I = GND$ to V_{CC} | <u>[5]</u> | | | | | | |
| | capacitance | output enabled | | - | 18 | - | - | - | pF |
| | | output disabled | | - | 5 | - | - | - | pF |

^[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

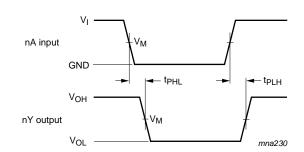
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

^[3] t_{en} is the same as t_{PZH} and t_{PZL} .

^[4] t_{dis} is the same as t_{PLZ} and t_{PHZ} .

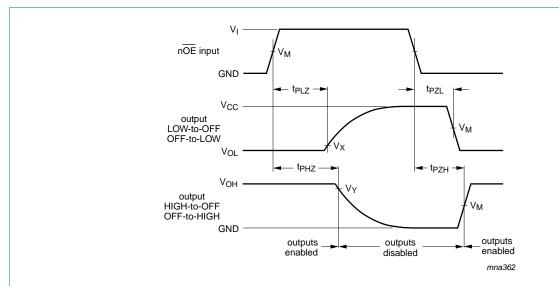
12. Waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. Propagation delay input (nA) to output (nY)



Measurement points are given in Table 9.

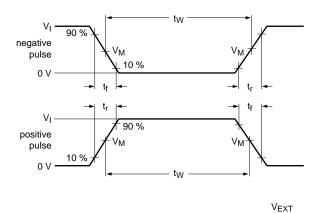
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

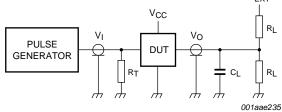
Fig 8. 3-state output enable and disable times

Table 9. Measurement points

| Supply voltage | Input | Output | Dutput | | | | | | |
|------------------|--------------------|--------------------|--------------------------|--------------------------|--|--|--|--|--|
| V _{CC} | V _M | V _M | V _X | V _Y | | | | | |
| 1.65 V to 1.95 V | 0.5V _{CC} | 0.5V _{CC} | V _{OL} + 0.15 V | V _{OH} – 0.15 V | | | | | |
| 2.3 V to 2.7 V | 0.5V _{CC} | 0.5V _{CC} | V _{OL} + 0.15 V | V _{OH} – 0.15 V | | | | | |
| 2.7 V | 1.5 V | 1.5 V | V_{OL} + 0.3 V | $V_{OH} - 0.3 V$ | | | | | |
| 3.0 V to 3.6 V | 1.5 V | 1.5 V | V _{OL} + 0.3 V | $V_{OH} - 0.3 V$ | | | | | |
| 4.5 V to 5.5 V | 0.5V _{CC} | 0.5V _{CC} | $V_{OL} + 0.3 V$ | $V_{OH} - 0.3 V$ | | | | | |

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Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistor.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 V_{EXT} = Test voltage for switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

| Supply voltage | Input | | Load | | V_{EXT} | V _{EXT} | | | |
|------------------|----------|--------------------------------|-------|----------------|-------------------------------------|-------------------------------------|--------------------|--|--|
| V _{CC} | VI | V_{l} t_{r}, t_{f} C_{l} | | R _L | t _{PLH} , t _{PHL} | t _{PZH} , t _{PHZ} | t_{PZL}, t_{PLZ} | | |
| 1.65 V to 1.95 V | V_{CC} | \leq 2.0 ns | 30 pF | 1 kΩ | open | GND | 2V _{CC} | | |
| 2.3 V to 2.7 V | V_{CC} | \leq 2.0 ns | 30 pF | 500Ω | open | GND | 2V _{CC} | | |
| 2.7 V | 2.7 V | \leq 2.5 ns | 50 pF | 500Ω | open | GND | 6 V | | |
| 3.0 V to 3.6 V | 2.7 V | \leq 2.5 ns | 50 pF | 500Ω | open | GND | 6 V | | |
| 4.5 V to 5.5 V | V_{CC} | ≤ 2.5 ns | 50 pF | 500Ω | open | GND | 2V _{CC} | | |

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

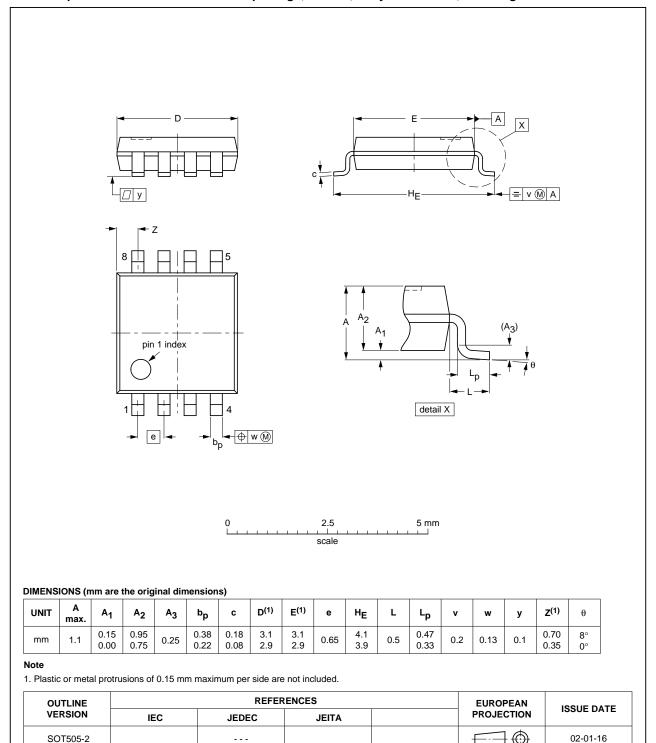
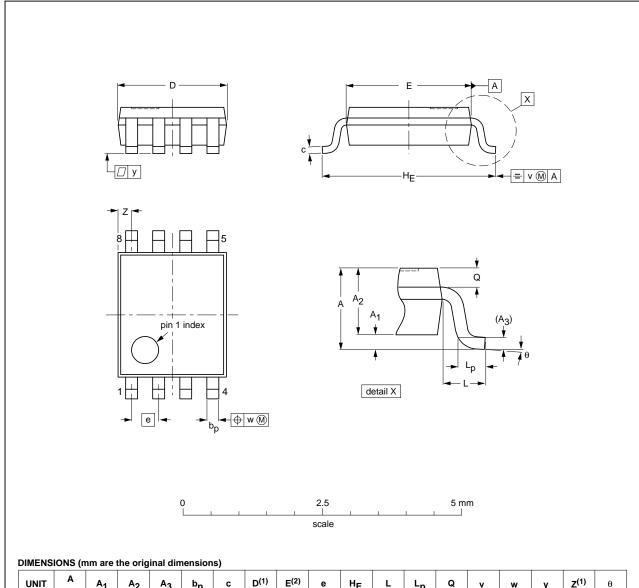


Fig 10. Package outline SOT505-2 (TSSOP8)

74LVC2G125 All information provided in this document is subject to legal disclaimers.

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



| UNIT | A max. | A ₁ | A ₂ | А3 | bp | С | D ⁽¹⁾ | E ⁽²⁾ | е | HE | L | Lp | Q | v | w | у | Z ⁽¹⁾ | θ |
|------|-----------|----------------|----------------|------|--------------|--------------|------------------|------------------|-----|------------|-----|--------------|--------------|-----|------|-----|------------------|----------|
| mm | 1 | 0.15 0.00 | 0.85 0.60 | 0.12 | 0.27 0.17 | 0.23 0.08 | 2.1 1.9 | 2.4 2.2 | 0.5 | 3.2 3.0 | 0.4 | 0.40 0.15 | 0.21 0.19 | 0.2 | 0.13 | 0.1 | 0.4 0.1 | 8° 0° |

Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

| OUTLINE | REFERENCES | | | | EUROPEAN | ISSUE DATE |
|----------|------------|--------|-------|--|------------|------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT765-1 | | MO-187 | | | | 02-06-07 |

Fig 11. Package outline SOT765-1 (VSSOP8)

74LVC2G125

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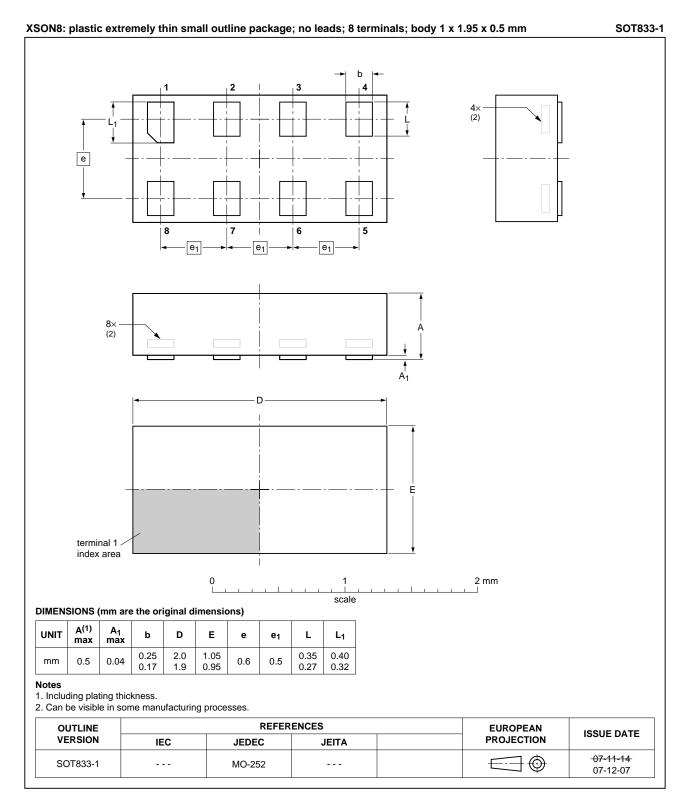


Fig 12. Package outline SOT833-1 (XSON8)

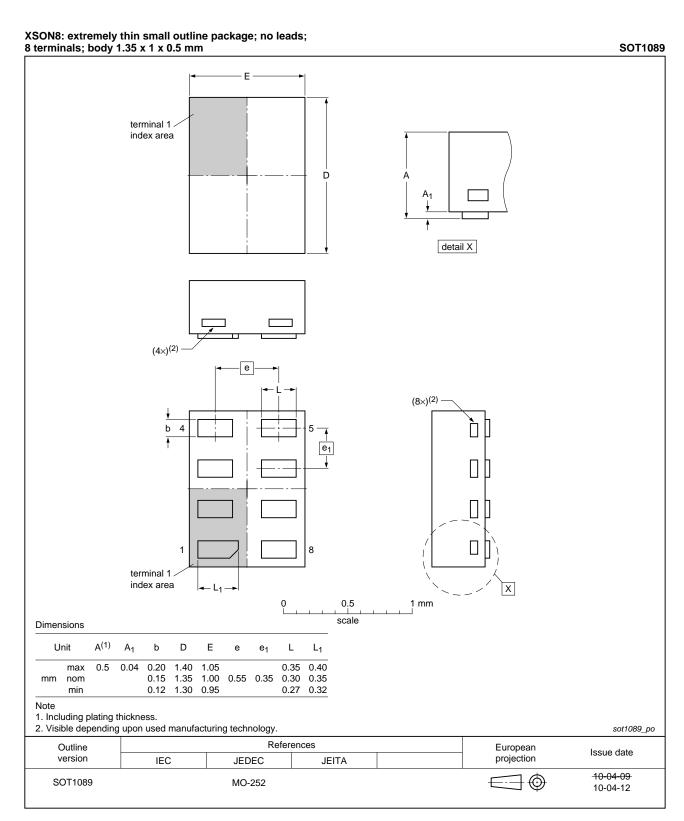


Fig 13. Package outline SOT1089 (XSON8)

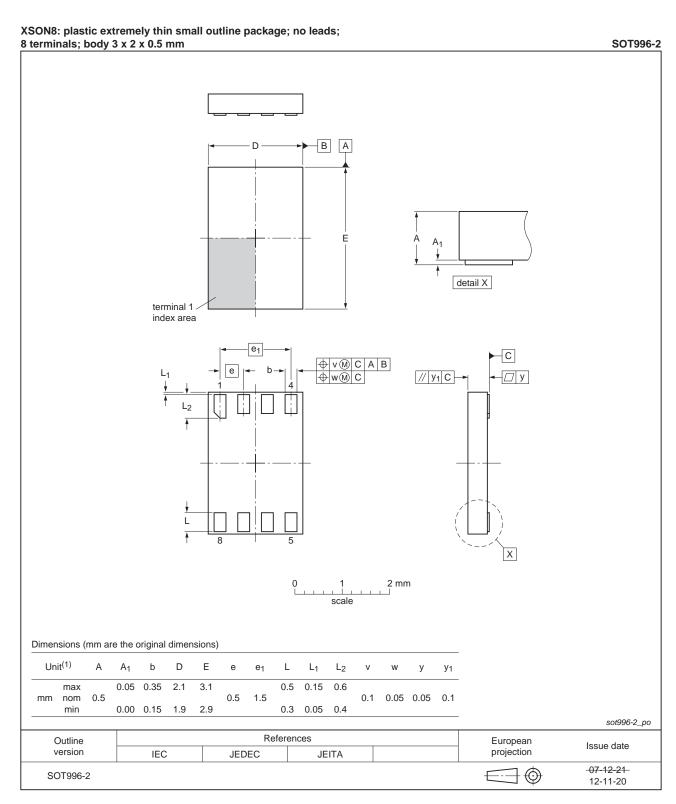


Fig 14. Package outline SOT996-2 (XSON8)

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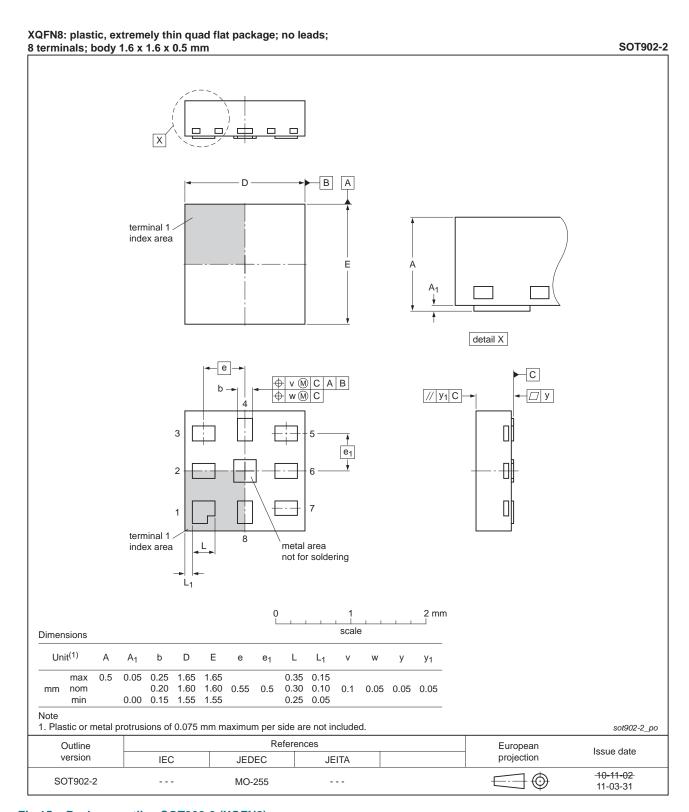


Fig 15. Package outline SOT902-2 (XQFN8)

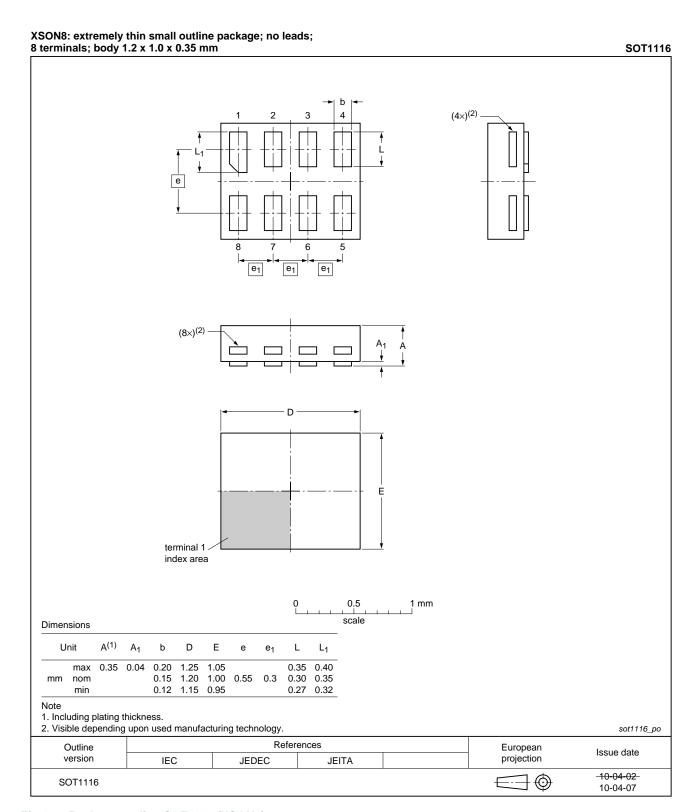


Fig 16. Package outline SOT1116 (XSON8)

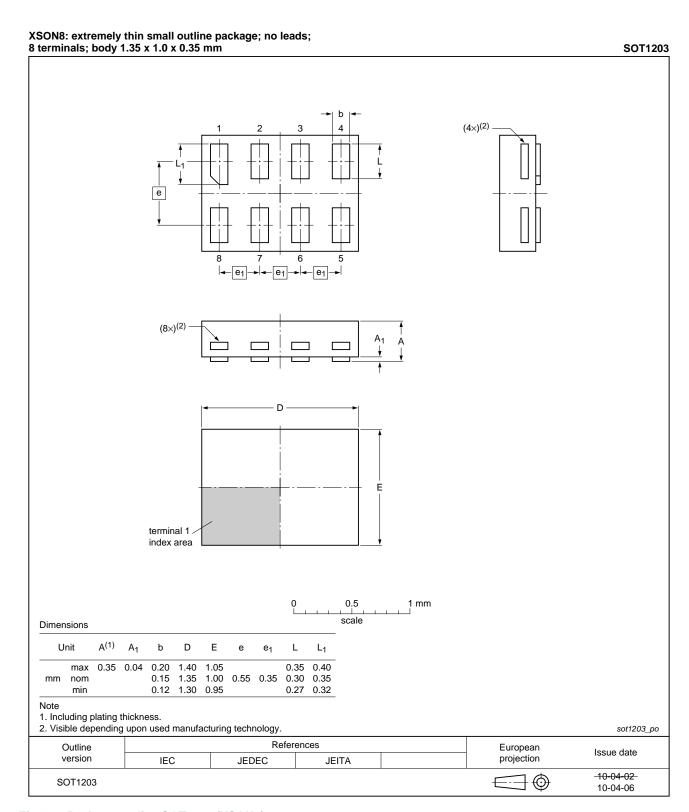


Fig 17. Package outline SOT1203 (XSON8)

Dual bus buffer/line driver; 3-state

14. Abbreviations

Table 11. Abbreviations

| Acronym | Description | |
|---------|---|--|
| CMOS | Complementary Metal-Oxide Semiconductor | |
| DUT | Device Under Test | |
| ESD | ElectroStatic Discharge | |
| НВМ | Human Body Model | |
| MM | Machine Model | |
| TTL | Transistor-Transistor Logic | |

15. Revision history

Table 12. Revision history

| | • | | | |
|-----------------|---------------------------------|-----------------------|----------------------|-----------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| 74LVC2G125 v.14 | 20130329 | Product data sheet | - | 74LVC2G125 v.13 |
| Modifications: | For type nu | mber 74LVC2G125GD XSO | N8U has changed to X | SON8. |
| 74LVC2G125 v.13 | 20120622 | Product data sheet | - | 74LVC2G125 v.12 |
| Modifications: | For type nu | mber 74LVC2G125GM the | SOT code has changed | to SOT902-2. |
| 74LVC2G125 v.12 | 20111201 | Product data sheet | - | 74LVC2G125 v.11 |
| Modifications: | Legal pages | s updated. | | |
| 74LVC2G125 v.11 | 20100909 | Product data sheet | - | 74LVC2G125 v.10 |
| 74LVC2G125 v.10 | 20080611 | Product data sheet | - | 74LVC2G125 v.9 |
| 74LVC2G125 v.9 | 20080226 | Product data sheet | - | 74LVC2G125 v.8 |
| 74LVC2G125 v.8 | 20070907 | Product data sheet | - | 74LVC2G125 v.7 |
| 74LVC2G125 v.7 | 20060523 | Product data sheet | - | 74LVC2G125 v.6 |
| 74LVC2G125 v.6 | 20051223 | Product data sheet | - | 74LVC2G125 v.5 |
| 74LVC2G125 v.5 | 20050201 | Product specification | - | 74LVC2G125 v.4 |
| 74LVC2G125 v.4 | 20040922 | Product specification | - | 74LVC2G125 v.3 |
| 74LVC2G125 v.3 | 20040109 | Product specification | - | 74LVC2G125 v.2 |
| 74LVC2G125 v.2 | 20030901 | Product specification | - | 74LVC2G125 v.1 |
| 74LVC2G125 v.1 | 20030310 | Product specification | - | - |
| | | | | |

16. Legal information

16.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Dual bus buffer/line driver; 3-state

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Dual bus buffer/line driver; 3-state

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